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1. (Amended) A charge transfer semiconductor device [including a crystalline semiconductor film having rod-like or columnar crystals extending in a predetermined direction, said device] comprising:

a crystalline semiconductor film having a plurality of crystals extending in a crystal growth direction;

a charge storing means including a plurality of photodetecting elements, each of said photodetecting elements being for storing a charge in accordance with an incident light; and

a charge transfer means for transferring said charge stored in said charge [stored] storing means,

wherein [said predetermined] the crystal growth direction coincides [or approximately coincides] with a charge transfer direction of the charge transfer means.

2. (Amended) A [charge transfer] semiconductor device [including a crystalline semiconductor film having rod-like or columnar crystals extending in a predetermined direction, said device] comprising:

a plurality of photodiodes being formed in a matrix on an insulating surface;

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~~a plurality of vertical charge coupled devices on the insulating surface, said vertical charge coupled devices being connected with the plurality of photodiodes;~~

~~at least a horizontal charge coupled device on the insulating surface, said horizontal charge coupled device being connected with the vertical charge coupled device,~~

~~wherein each of the vertical and horizontal charge coupled devices comprises a crystalline semiconductor film having a plurality of crystals extending in a crystal growth direction,~~

~~wherein [said predetermined] the crystal growth direction coincides [or approximately coincides] with a charge transfer direction of each of the vertical and horizontal charge coupled devices.~~

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5. (Amended) A device according to claim 1 further comprising an active matrix display device being integrated with said charge transfer means [on the] over a same substrate.

6. (Amended) A device according to claim 2 further comprising an active matrix display device being integrated with said vertical and horizontal charge coupled devices [on the] over a same substrate.

7. (Amended) A method of manufacturing a charge transfer semiconductor device, [including a crystalline semiconductor film having rod-like or columnar crystals extending in a predetermined direction,] said method comprising the steps of:

forming an amorphous semiconductor film on an insulating surface;

selectively introducing a metal element for promoting crystallization of said semiconductor in contact with a [predetermined region] portion of said amorphous semiconductor film;

heating the amorphous semiconductor film so that [to grow crystals] a plurality of crystals grow in a crystal growth direction parallel with said insulating surface from [said predetermined] the portion [whereby said] to form a crystalline semiconductor film [is formed];

heating said crystalline semiconductor film in an oxidizing atmosphere including a halogen element to form a thermal oxidation film on a surface of the semiconductor film;

removing said thermal oxidation film; and

forming at least a charge coupled device for transferring a charge in a charge transfer direction that coincides [or approximately coincides] with [said predetermined] the crystal growth direction.